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(19) **United States**(12) **Patent Application Publication** (10) **Pub. No.: US 2022/0407487 A1**
LIU (43) **Pub. Date: Dec. 22, 2022**(54) **METHOD FOR FORMING BULK ACOUSTIC WAVE RESONANCE DEVICE**(71) Applicant: **CHANGZHOU CHEMSEMI CO., LTD.**, Changzhou (CN)(72) Inventor: **Yuhao LIU**, Shanghai (CN)(21) Appl. No.: **17/640,338**(22) PCT Filed: **Sep. 5, 2019**(86) PCT No.: **PCT/CN2019/104600**

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A method for forming a bulk acoustic wave resonance device, comprising: (S201) forming a first layer, which comprises: providing a first substrate; forming a piezoelectric layer located on the first substrate; forming a first electrode layer located on the piezoelectric layer; and forming a cavity pre-treatment layer located on the piezoelectric layer, used for forming a cavity, and at least covering a first end of the first electrode layer, wherein a first side of the first layer corresponds to the side of the first substrate; a second side of the first layer corresponds to the side of the cavity pre-treatment layer; (S203) forming a second layer, which comprises: providing a second substrate; (S205) connecting the first layer to the second layer, the second layer being located at the second side; (S207) removing the first substrate, so that the first side corresponds to the side of the piezoelectric layer; and (S209) forming a second electrode layer located at the first side and contacting with the piezoelectric layer. The formed piezoelectric layer does not comprise a crystal that is significantly turned so as to facilitate increasing the electromechanical coupling coefficient and the Q value of the resonance device. In addition, the second substrate processing and the active layer processing can be respectively performed, and are flexible.

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